

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 240416US0DIV		SERIAL NO. 10/618,085	
<div style="display: flex; align-items: center; justify-content: center;"> <div style="border: 2px solid black; border-radius: 50%; padding: 10px; text-align: center; margin: 0 10px;"> O I P E FEB 01 2005 PATENT & TRADEMARK OFFICE </div> <div> LIST OF REFERENCES CITED BY APPLICANT </div> </div>				APPLICANT Masakazu KANECHIKA, et al.			
				FILING DATE July 14, 2003		GROUP 2813	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
	AO	JP8-306752	11-22-96	JAPAN (with English Abstract)			
	AP	JP7-118100	05-09-95	JAPAN (with English Abstract)			
	AQ	JP8-203863	08-09-96	JAPAN (with English Abstract)			
	AR	JP9-232482	09-05-97	JAPAN (with English Abstract)			
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW	Hayakawa et al; "Mechanism of Residue Formation in Silicon Trench Etching Using a Bromine-Based Plasma," Jpn. J. Appl. Phys., Vol. 37 (1998) pp. 5-9.					
	AX						
	AY						
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner					Date Considered		
<small>*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							

COPY